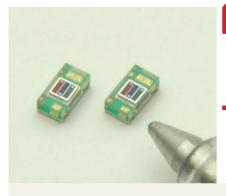


Si photodiode



S10942-01CT

RGB color sensor integrated in small and thin package

The S10942-01CT is a color sensor molded into a plastic package having a 3-channel (RGB) photodiode sensitive to the Red (λ =590 nm Min.), Green (λ =480 to 600 nm) and Blue (λ =400 to 540 nm) regions of the spectrum. When compared to the previous model (S9702), the S10942-01CT is significantly miniaturized the package size by 80% in cubic volume and PC board mount space by 77% in area. The S10942-01CT is ideal for RGB-LCD backlight monitors installed in such as mobile phones.

- Features

- **■** Small, thin package: 3.0 × 1.6 × 10 tmm
- **⇒** 3-channel (RGB) Si photodiode
- → Photosensitive area: 1 × 1 mm/3-segment (RGB)
- RoHS compliant
- Surface mount type

Applications

- **■** Portable or mobile equipment
- RGB-LCD backlight monitors
- **Detectors for various light sources**
- Color detection

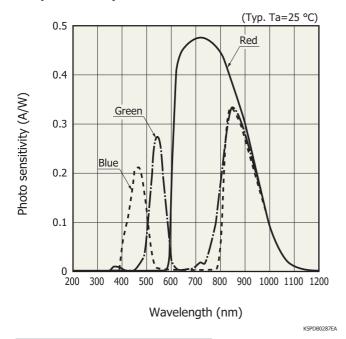
Absolute maximum ratings

Parameter	Symbol	Value	Unit
Reverse voltage	VR Max.	10	V
Operating temperature	Topr	-25 to +85	°C
Storage temperature	Tstg	-40 to +85	°C

■ Electrical and optical characteristics (Ta = 25 °C, per element)

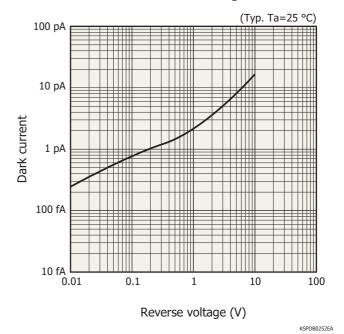
Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit			
		Blue	-	400 to 540 800 to 1000	-				
Spectral response range	λ	Green	-	480 to 600 760 to 1000	-	nm			
		Red	-	590 to 1000	-	1			
	S	Blue (λ=460 nm)	0.16	0.21	0.26				
Photo sensitivity		Green (λ=540 nm)	0.30	A/W					
		Red (λ=640 nm)	0.40	0.45	0.50				
Dark current	ID	VR=1 V, All elements	-	1	50	pА			
Temperature coefficient of ID	TCID		-	1.12	-	times/°C			
Rise time	tr	$VR=0$ V, $RL=1$ $k\Omega$, 10 to 90%	-	0.1	1.0	μs			
Terminal capacitance Ct V		VR=0 V, f=10 kHz	5	12	25	pF			

Spectral response

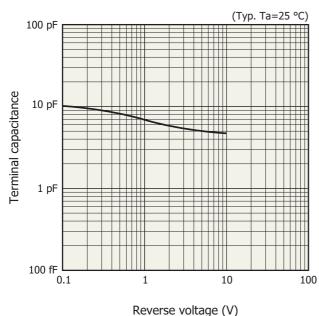


Since this photodiode has sensitivity in the infrared region, infrared light must be filtered out as needed.

Dark current vs. reverse voltage

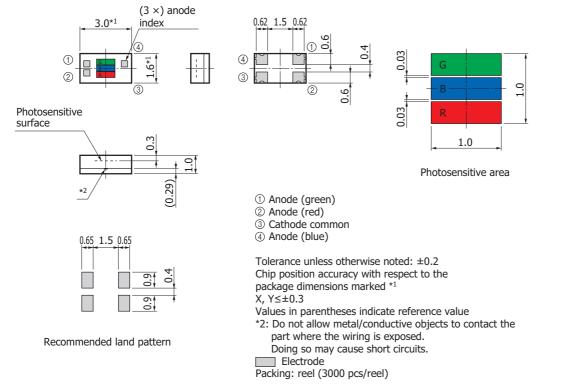


Terminal capacitance vs. reverse voltage



KSPDB0253EA

Dimensional outline (uint: mm)



KSPDA0186E

■ Line-up of RGB color sensors

Type no.	Туре	Photosensitive area size (mm)	Package (mm)	ser wav	Peak sitivity elength nm)	tivity Photo sensitivity ength		/	Photo			
S9032-02	Photodiode	ф2.0	$4 \times 4.8 \times 1.8^{t}$ 6-pin (filter 0.75 ^t)	B G R	460 540 620	B G R		0.18 (A/W 0.23 (A/W 0.16 (A/W	<u>)</u> [λ	=54	10 nm]	
S9702	Photodiode	1.0 × 1.0	3 × 4 × 1.3 ^t 4-pin (filter 0.75 ^t)	B G R	460 540 620	B G R		0.18 (A/W 0.23 (A/W 0.16 (A/W	<u>)</u> [λ	=54	10 nm]	
S10917-35GT	Photodiode	1.0 × 1.0	$3 \times 1.6 \times 1.0^{t}$ COB (on-chip filter)	B G R	460 540 620	B G R		0.2 (A/W) 0.23 (A/W 0.17 (A/W	<u> </u>	_=54	10 nm]	
S10942-01CT	Photodiode	1.0 × 1.0	$3 \times 1.6 \times 1.0^{t}$ COB (on-chip filter)		*	B G R		0.21 (A/W 0.25 (A/W 0.45 (A/W) [λ) [λ	.=46 .=54	60 nm] 10 nm]	
S9706	Digital photo IC	1.2 × 1.2	4 × 4.8 × 1.8 ^t 6-pin (filter 0.75 ^t)	B G R	465 540 615	Low	B G R	0.21 (LSB/lx) 0.45 (LSB/lx) 0.64 (LSB/lx)	High	B G R	1.9 (LSB/lx) 4.1 (LSB/lx) 5.8 (LSB/lx)	
S11012-01CR	Digital photo IC	1.2 × 1.2	$3.43 \times 3.8 \times 1.6^{t}$ COB (on-chip filter)	B G R	465 540 615	Low	B G R	0.3 (LSB/lx) 0.6 (LSB/lx) 1.4 (LSB/lx)	High	B G R	2.6 (LSB/lx) 5.3 (LSB/lx) 12.9 (LSB/lx)	

^{*} Refer to "Spectral response" of "Si photodiode S10942-01CT" datasheet.

Information described in this material is current as of October, 2011.

Product specifications are subject to change without prior notice due to improvements or other reasons. Before assembly into final products, please contact us for the delivery specification sheet to check the latest information.

Type numbers of products listed in the delivery specification sheets or supplied as samples may have a suffix "(X)" which means preliminary specifications or a suffix "(Z)" which means developmental specifications.

The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product

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